

NTE226 Germanium PNP Transistor Audio Power Amp

Description:

The NTE226 is a Germanium PNP transistor in a TO66 type package designed for high-fidelity, high-power output applications.

Absolute Maximum Ratings:

Collector-Base Voltage, V_{CBO}	35V
Collector-Emitter Voltage ($R_{BE} = 100\Omega$), V_{CER}	35V
Emitter-Base Voltage, V_{EBO}	6V
Collector Current, I_C	2A
Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	12W
Operating Junction Temperature, T_J	+85°C
Storage Temperature Range, T_{stg}	-55° to +85°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 25V, I_E = 0$	-	-	200	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 6V, I_C = 0$	-	-	200	μA
DC Current Gain	h_{FE}	$V_{CE} = 1.5V, I_C = 200\text{mA}$	50	100	275	
Small-Signal Current Gain Resistance	f_{ob}	$V_{CE} = 1.5V, I_C = 200\text{mA}$	-	0.7	-	MHz
Base Spreading Resistance	r_{bb}	$V_{CE} = 1.5V, I_C = 200\text{mA}, f = 6\text{MHz}$	-	15	-	Ω

